

Phase Control Thyristors (Stud Version), 300 A


TO-118 (TO- 209AE)

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	300 A
V_{DRM}/V_{RRM}	400 V, 800 V, 1200 V, 1600 V, 1800 V, 2000 V
V_{TM}	1.28 V
I_{GT}	200 mA
T_J	-40 °C to +125 °C
Package	TO-118 (TO-209AE)
Circuit configuration	Single SCR

FEATURES

- Center amplifying gate
- International standard case TO-118 (TO-209AE)
- Hermetic metal case with ceramic insulator
- Threaded studs UNF 3/4"-16UNF-2A or ISO M24 x 1.5
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		300	A
	T_C	75	°C
$I_{T(RMS)}$		470	A
I_{TSM}	50 Hz	8000	
	60 Hz	8380	
I^2t	50 Hz	320	kA ² s
	60 Hz	292	
V_{DRM}/V_{RRM}		400 to 2000	V
t_q	Typical	100	μs
T_J		-40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST300S	04	400	500	50
	08	800	900	
	12	1200	1300	
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	I _{T(AV)}	180° conduction, half sine wave			300	A
					75	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 64 °C case temperature			470	A
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	8000	
		t = 8.3 ms			8380	
		t = 10 ms	100 % V _{RRM} reapplied		6730	
		t = 8.3 ms			7040	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		320	kA ² s
		t = 8.3 ms			292	
		t = 10 ms	100 % V _{RRM} reapplied		226	
		t = 8.3 ms			207	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied			3200	kA ² √s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.97	V
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum			0.98	
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum			0.74	mΩ
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum			0.73	
Maximum on-state voltage	V _{TM}	I _{pk} = 940 A, T _J = T _J maximum, t _p = 10 ms sine pulse			1.66	V
Maximum holding current	I _H	T _J = 25 °C, anode supply 12 V resistive load			600	mA
Typical latching current	I _L				1000	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C	1.0	μs
Typical turn-off time	t_q	$I_{TM} = 550$ A, $T_J = T_J$ maximum, $di/dt = 40$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs	100	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	2.0		
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	3.0		A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	20		V
Maximum peak negative gate voltage	$-V_{GM}$		5.0		
DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	200	-	mA
		$T_J = 25$ °C	100	200	
		$T_J = 125$ °C	50	-	
DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C	2.5	-	V
		$T_J = 25$ °C	1.8	3	
		$T_J = 125$ °C	1.1	-	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	10		mA
DC gate voltage not to trigger	V_{GD}		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		-40 to 125	°C
Maximum storage temperature range	T_{Stg}		-40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.10	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.03	
Mounting torque, ± 10 %		Non-lubricated threads	48.5 (425)	N · m (lbf · in)
Approximate weight			535	g
Case style		See dimensions - link at the end of datasheet	TO-118 (TO-209AE)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.011	0.008	$T_J = T_J$ maximum	K/W
120°	0.013	0.014		
90°	0.017	0.018		
60°	0.025	0.026		
30°	0.041	0.042		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

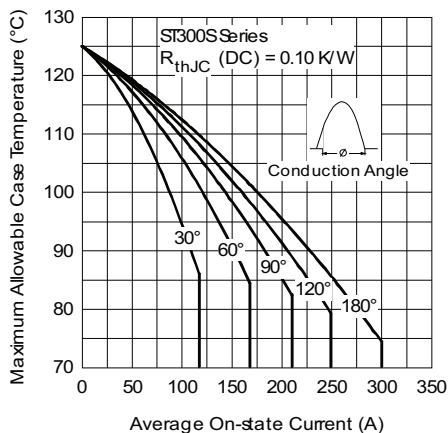


Fig. 1 - Current Ratings Characteristics

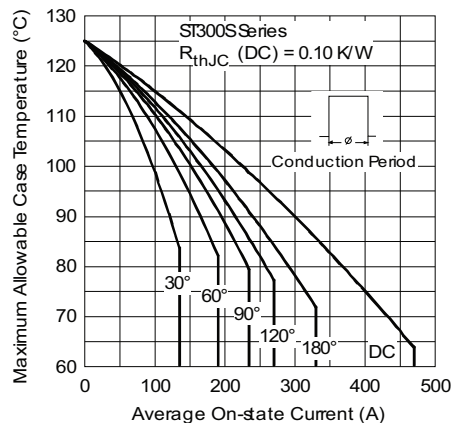


Fig. 2 - Current Ratings Characteristics

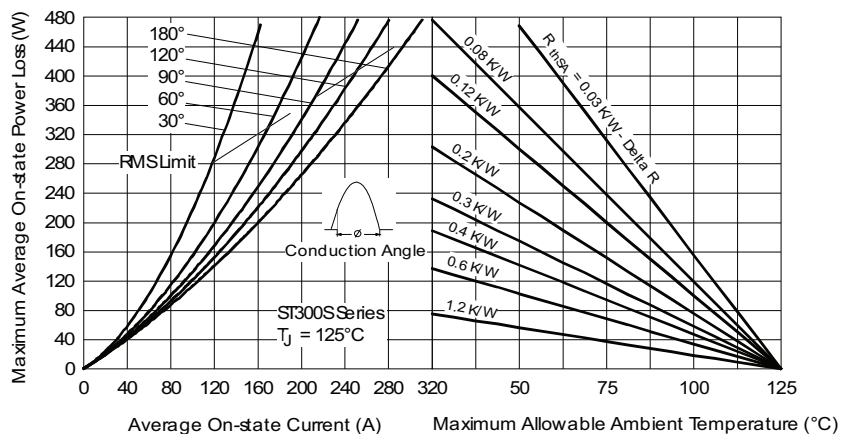


Fig. 3 - On-State Power Loss Characteristics

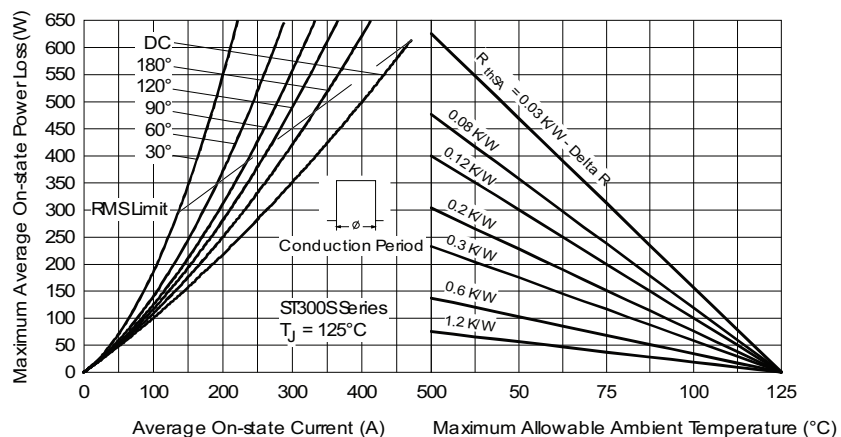


Fig. 4 - On-State Power Loss Characteristics

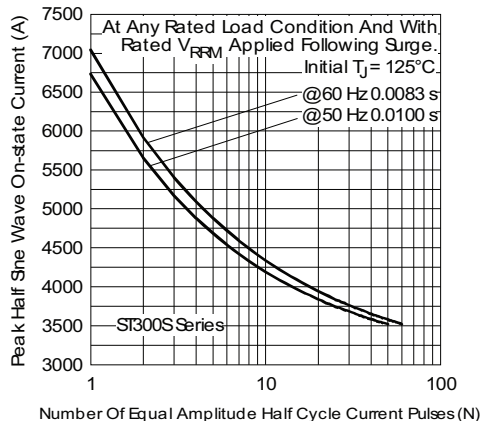


Fig. 5 - Maximum Non-Repetitive Surge Current

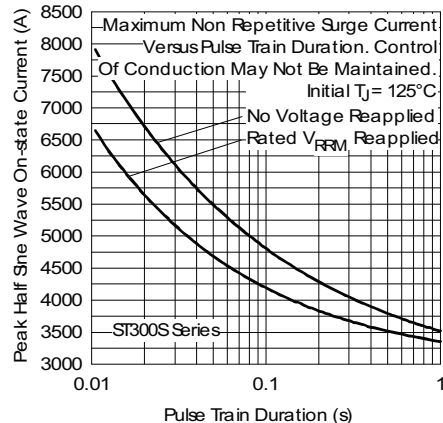


Fig. 6 - Maximum Non-Repetitive Surge Current

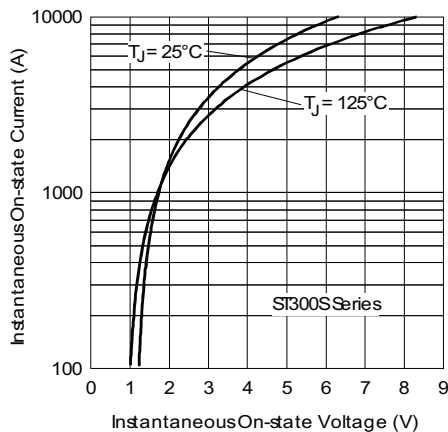
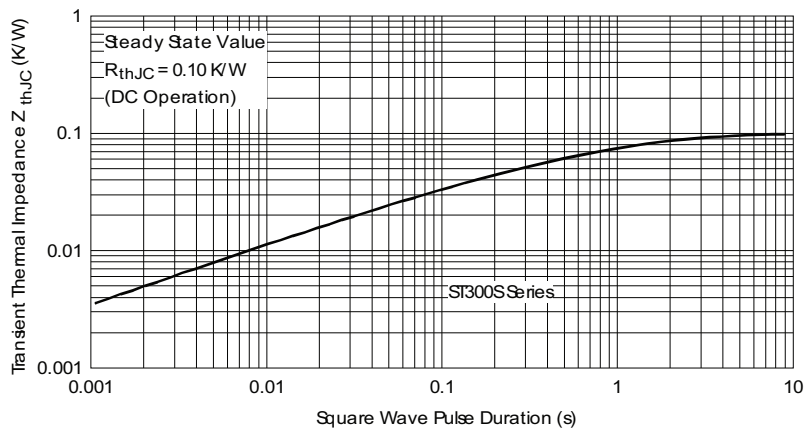


Fig. 7 - On-State Voltage Drop Characteristics


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

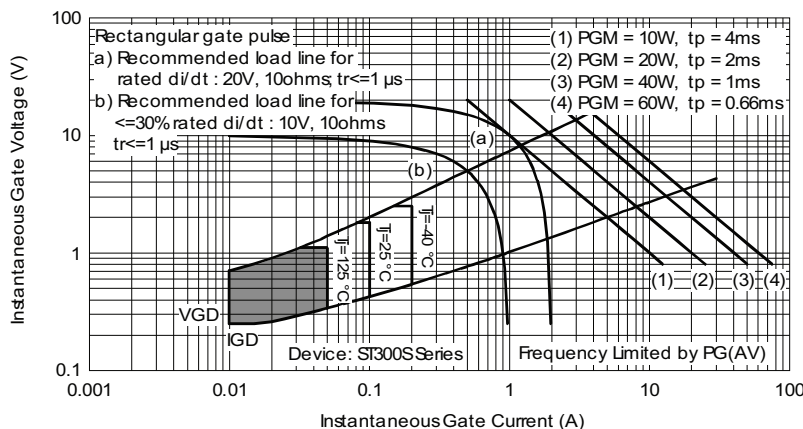


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

VS-	ST	30	0	S	20	P	0	-	PbF
1	2	3	4	5	6	7	8	9	10

- 1 - Vishay Semiconductors product
- 2 - Thyristor
- 3 - Essential part number
- 4 - 0 = Converter grade
- 5 - S = Compression bonding stud
- 6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7 - P = stud base 3/4" 16UNF-2A threads
M = stud base metric threads (M24 x 1.5)
- 8 - 0 = Eyelet terminals (gate and auxiliary cathode leads)
1 = Fast-on terminals (gate and auxiliary cathode leads)
3 = Threaded top terminal 3/8" 24UNF-2A
- 9 - Critical dV/dt : • None = 500 V/ μs (standard value)
• L = 1000 V/ μs (special selection)
- 10 - None = Standard production
PbF = Lead (Pb)-free

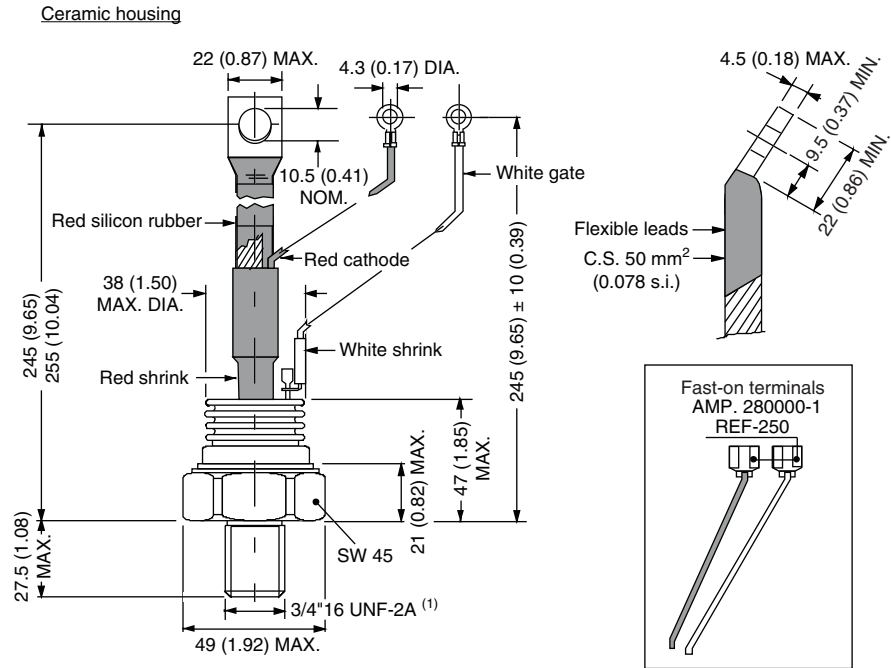
LINKS TO RELATED DOCUMENTS

Dimensions

www.vishay.com/doc?95084

TO-209AE (TO-118)

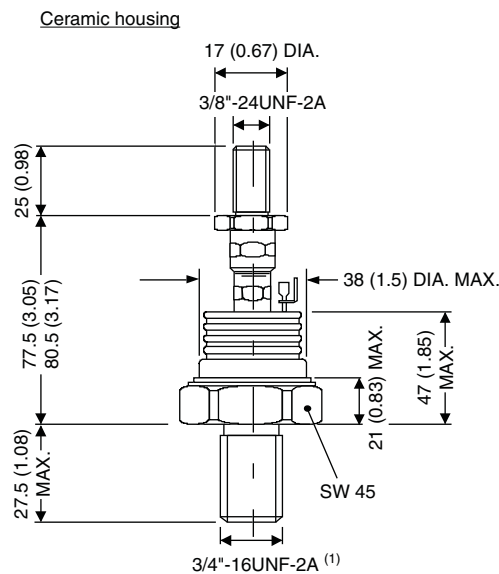
DIMENSIONS - TO-209AE (TO-118) in millimeters (inches)



Note

(1) For metric device: M24 x 1.5 - length screw 21 (0.83) maximum

DIMENSIONS - TO-209AE (TO-118) WITH TOP THREAD TERMINAL 3/8" in millimeters (inches)



Note

(1) For metric device: M24 x 1.5 - length screw 21 (0.83) maximum



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